



**PRODUCT NAME** : 2SB544 PNP General Purpose Transistor

**PRICE** : Rs 25.00

**SKU** : RM2140



## DESCRIPTION

## Features

- Collector-Emitter Volt ( $V_{ce0}$ ): 25V
- Collector-Base Volt ( $V_{cb0}$ ): 25V
- Collector Current ( $I_c$ ): 1.0A
- $h_{fe}$ : 60-560 @ 50mA
- Power Dissipation ( $P_{tot}$ ): 900mW
- Current-Gain-Bandwidth ( $f_{total}$ ): 180MHz
- Type: PNP

Ordering number: EN 199J

<b>SANYO</b>	No.199J	<h2 style="margin: 0;">2SB544/2SD400</h2> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <p style="margin: 0;">Low-Frequency Power Amp, Electronic Governor Applications</p>
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( ): 2SB544

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	(-)25	V
Collector to Emitter Voltage	V <sub>CE0</sub>	(-)25	V
Emitter to Base Voltage	V <sub>EB0</sub>	(-)5	V
Collector Current	I <sub>C</sub>	(-)1	A
Collector Current(Pulse)	I <sub>CP</sub>	(-)2	A
Collector Dissipation	P <sub>C</sub>	900	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

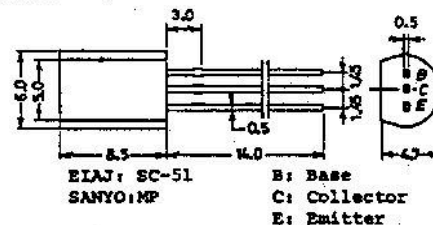
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = (-)20V, I <sub>E</sub> = 0			(-)1.0	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = (-)4V, I <sub>C</sub> = 0			(-)1.0	μA
DC Current Gain	h <sub>FE</sub> (1)	V <sub>CE</sub> = (-)2V, I <sub>C</sub> = (-)50mA	60*		560*	
	h <sub>FE</sub> (2)	V <sub>CE</sub> = (-)2V, I <sub>C</sub> = (-)1A	30			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = (-)10V, I <sub>C</sub> = (-)50mA		180		MHz
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> = (-)10V, f = 1MHz		(25)		pF
				15		
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = (-)500mA, I <sub>B</sub> = (-)50mA	(-0.15)		(-0.7)	V
			0.1		0.3	
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = (-)500mA, I <sub>B</sub> = (-)50mA	(-0.85)		(-1.2)	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = (-)10μA, I <sub>E</sub> = 0	(-)25			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = (-)1mA, R <sub>BE</sub> = ∞	(-)25			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = (-)10μA, I <sub>C</sub> = 0	(-)5			V

\* : The 2SB544/2SD400 are classified by 50mA h<sub>FE</sub> as follows :

60 D 120	100 E 200	160 F 320	280 G 560
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**Case Outline 2006A**  
(unit: mm)



Specifications and information herein are subject to change without notice.

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